

New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
 SPRINGFIELD, NEW JERSEY 07081
 U.S.A.

SILICON
 GENERAL
 PURPOSE
 TRANSISTORS

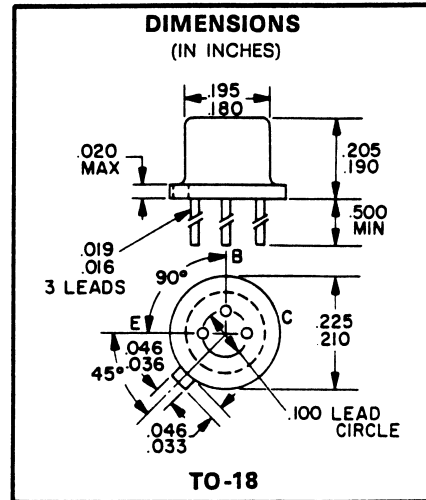
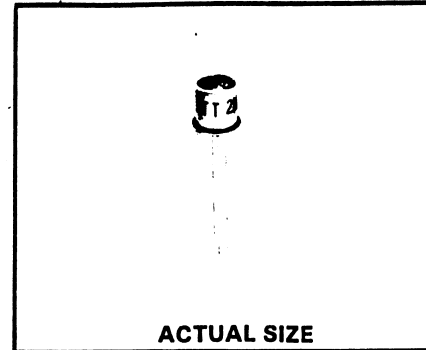
2N2509

3301 ELECTRONICS WAY • WEST PALM BEACH • FLORIDA 33407

LOW LEVEL LOW NOISE NPN SILICON PLANAR TRANSISTORS

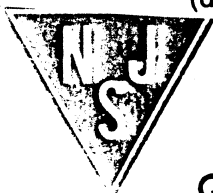
- High V_{CE0} ; 80 Vdc min.
- Low Noise; 7 dB max. @ $10\mu A$
- Low I_{CBO} ; 5nA max. @ 100 Vdc

The ITT 2N2509 is an NPN silicon planar transistor designed for application in low noise, low level amplifiers in the audio through high frequency range.



ABSOLUTE MAXIMUM RATINGS

CHARACTERISTICS		UNITS
Collector-to-Base Voltage	125	Volts
Collector-to-Emitter Voltage (open base)	80	Volts
Emitter-to-Base Voltage	7	Volts
Collector Current (continuous)	30	mA
Junction Temperature (operating)	-65 to +175	°C
(storage)	-65 to +200	°C
Total Power Dissipation @ $T_c = 25^\circ C$ (derate 6.85 mW/°C above 25°C)	1.2	Watts
Total Power Dissipation @ $T_A = 25^\circ C$ (derate 2.06 mW/°C above 25°C)	0.36	Watts



Quality Semi-Conductors